

FQP3N60C

N-Channel QFET® MOSFET

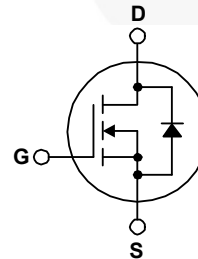
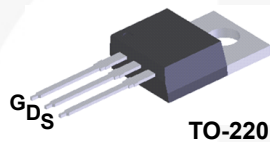
600 V, 3.0 A, 3.4 Ω

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 3.0 A, 600 V, $R_{DS(on)} = 3.4 \Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 1.5 \text{ A}$
- Low Gate Charge (Typ. 10.5 nC)
- Low Crss (Typ. 5.0 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP3N60C	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	3 1.8	A A
I_{DM}	Drain Current - Pulsed (Note 1)	12	A
V_{GSS}	Gate-Source voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	150	mJ
I_{AR}	Avalanche Current (Note 1)	3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	75 0.62	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQP3N60C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.67	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3N60C	FQP3N60C	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V V _{DS} = 480 V, T _C = 125°C	--	--	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1.5 A	--	2.8	3.4	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 1.5 A	--	3.5	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	435	565	pF
C _{oss}	Output Capacitance		--	45	60	pF
C _{rss}	Reverse Transfer Capacitance		--	5	8	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 3 A R _G = 25 Ω	--	12	34	ns
t _r	Turn-On Rise Time		--	30	70	ns
t _{d(off)}	Turn-Off Delay Time		--	35	80	ns
t _f	Turn-Off Fall Time		(Note 4)	--	35	80
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 3 A V _{GS} = 10 V	--	10.5	14	nC
Q _{gs}	Gate-Source Charge		--	2.1	--	nC
Q _{gd}	Gate-Drain Charge		(Note 4)	--	4.5	--
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	3	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	12	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 3 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 3 A di _F /dt = 100 A/μs	--	260	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.6	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 30 mH, I_{AS} = 3 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 3 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

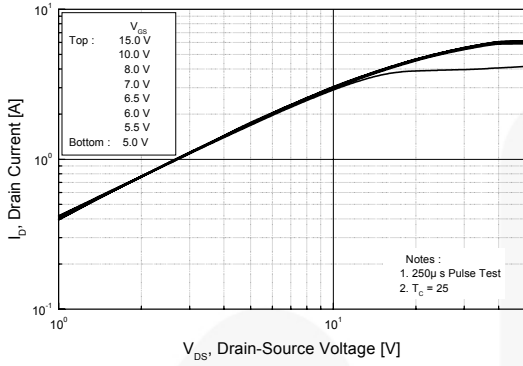


Figure 2. Transfer Characteristics

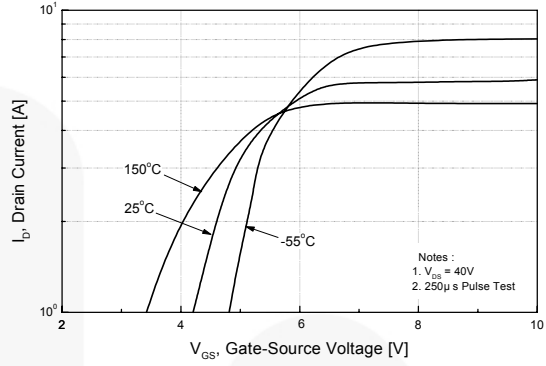


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

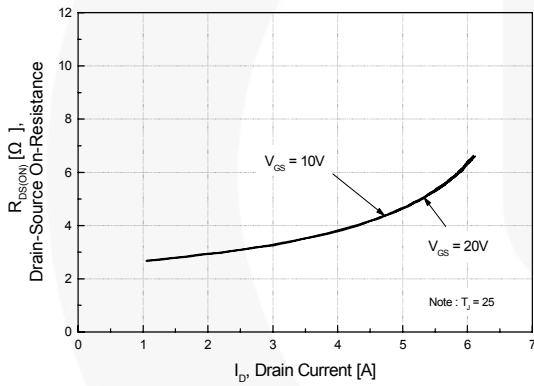


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

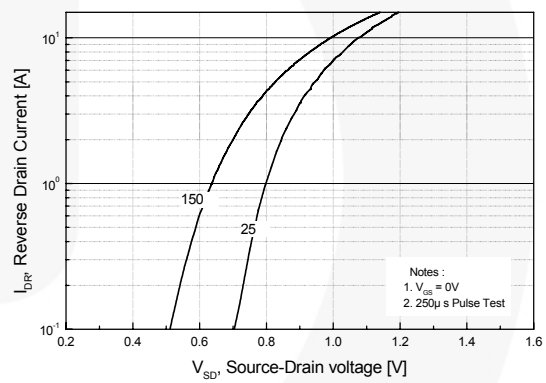


Figure 5. Capacitance Characteristics

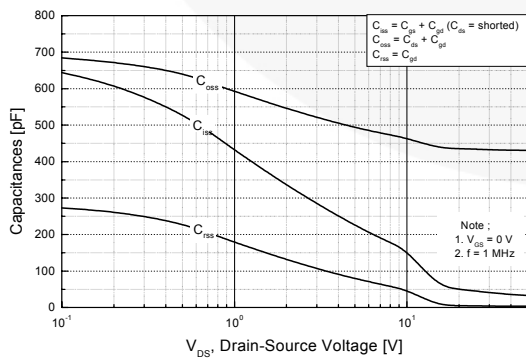
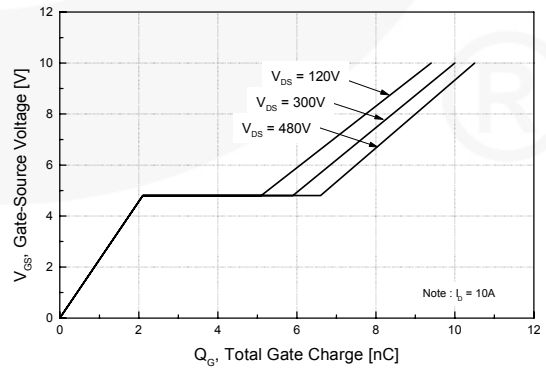


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

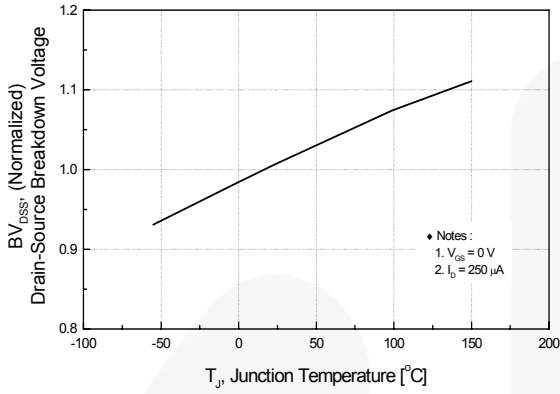


Figure 8. On-Resistance Variation vs. Temperature

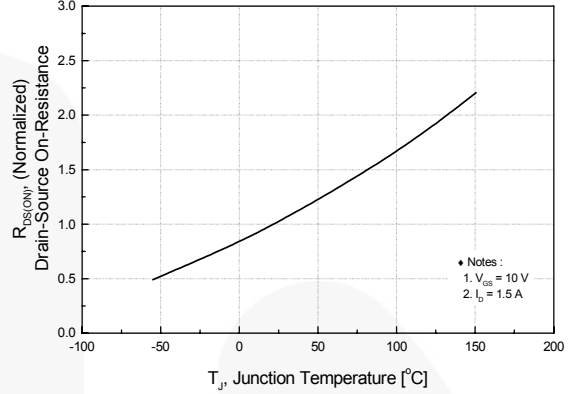


Figure 9. Maximum Safe Operating Area

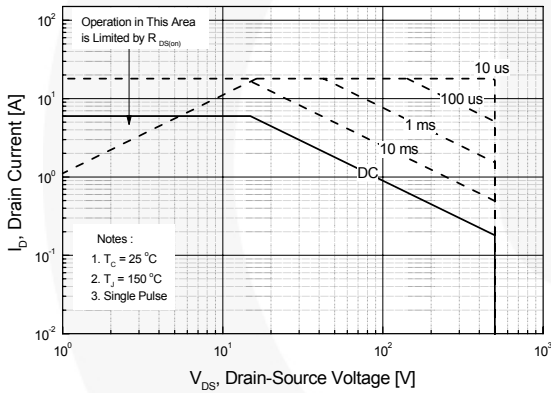


Figure 10. Maximum Drain Current vs. Case Temperature

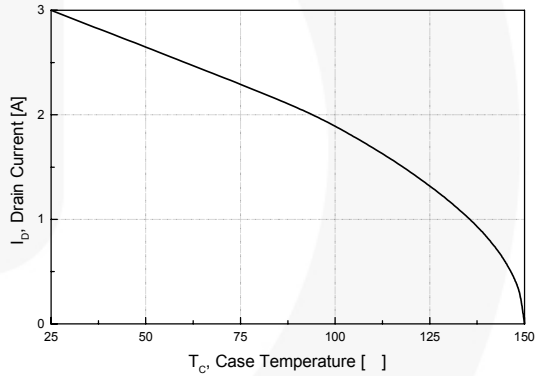
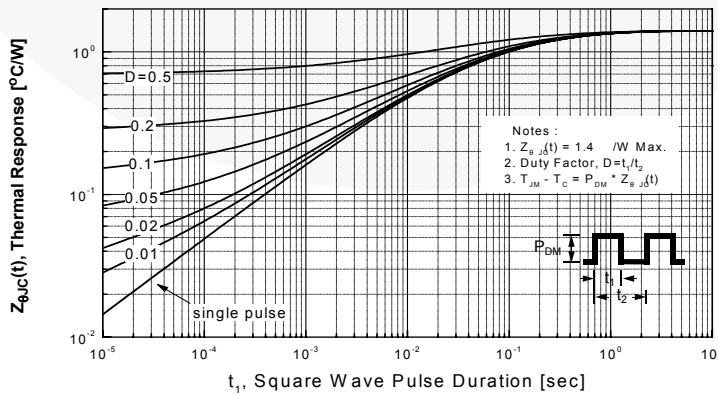


Figure 11. Transient Thermal Response Curve



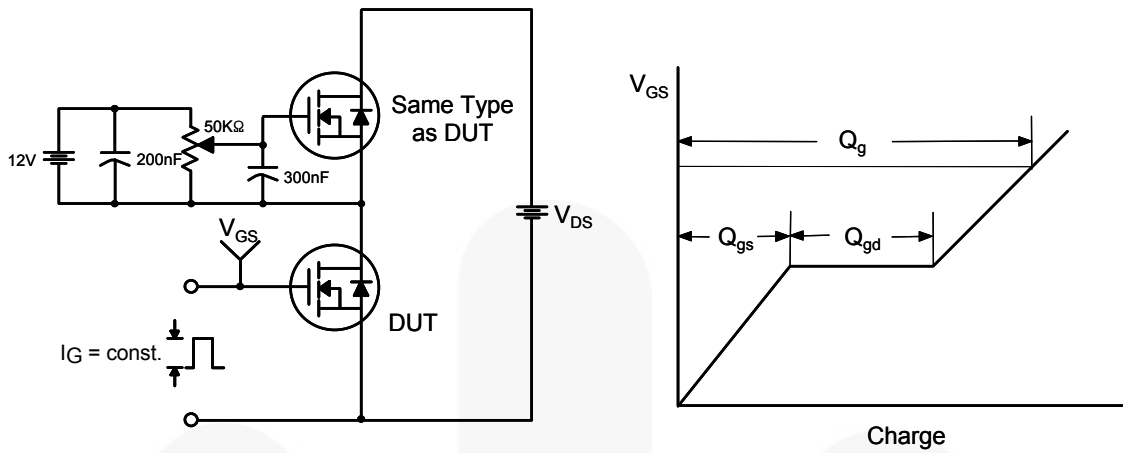


Figure 12. Gate Charge Test Circuit & Waveform

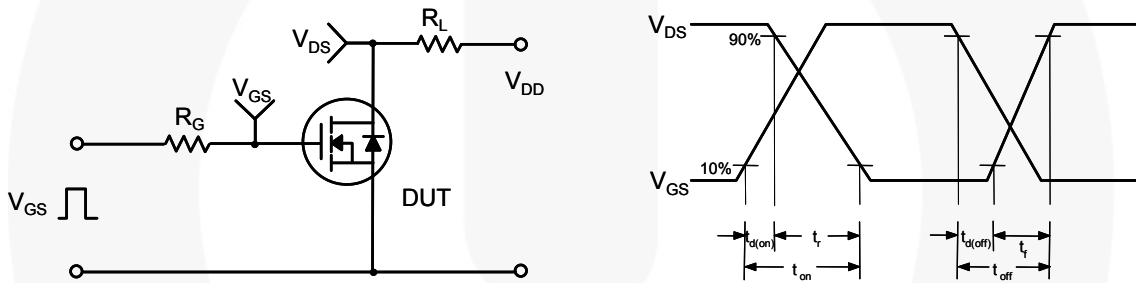


Figure 13. Resistive Switching Test Circuit & Waveforms

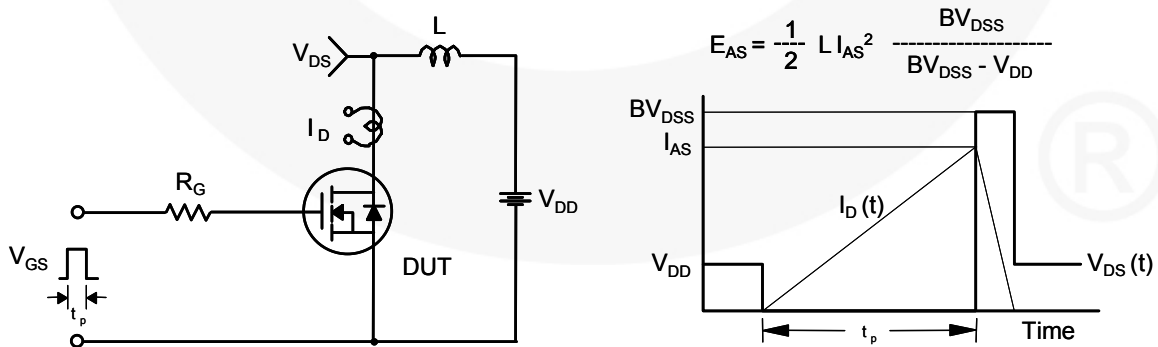


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

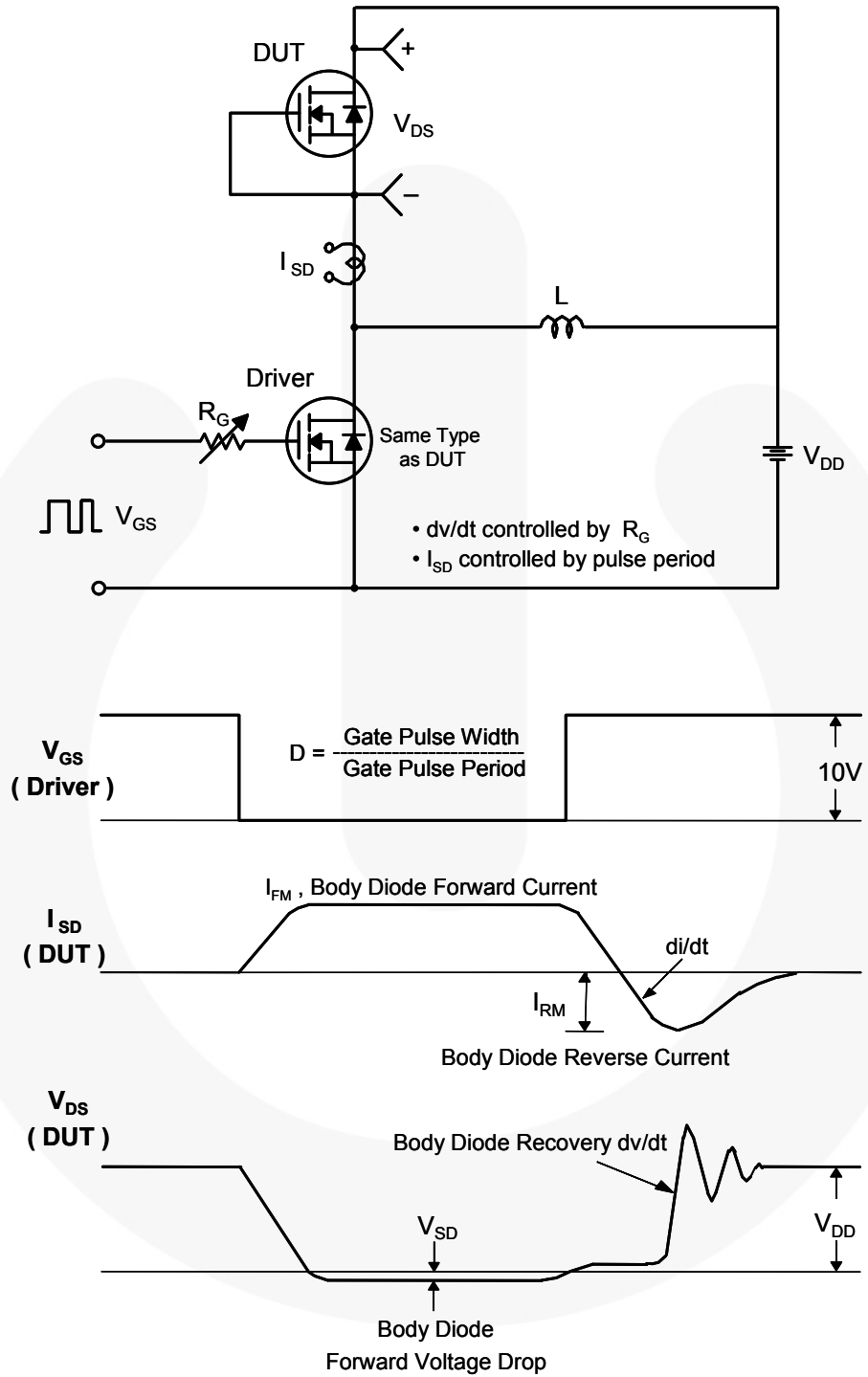


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

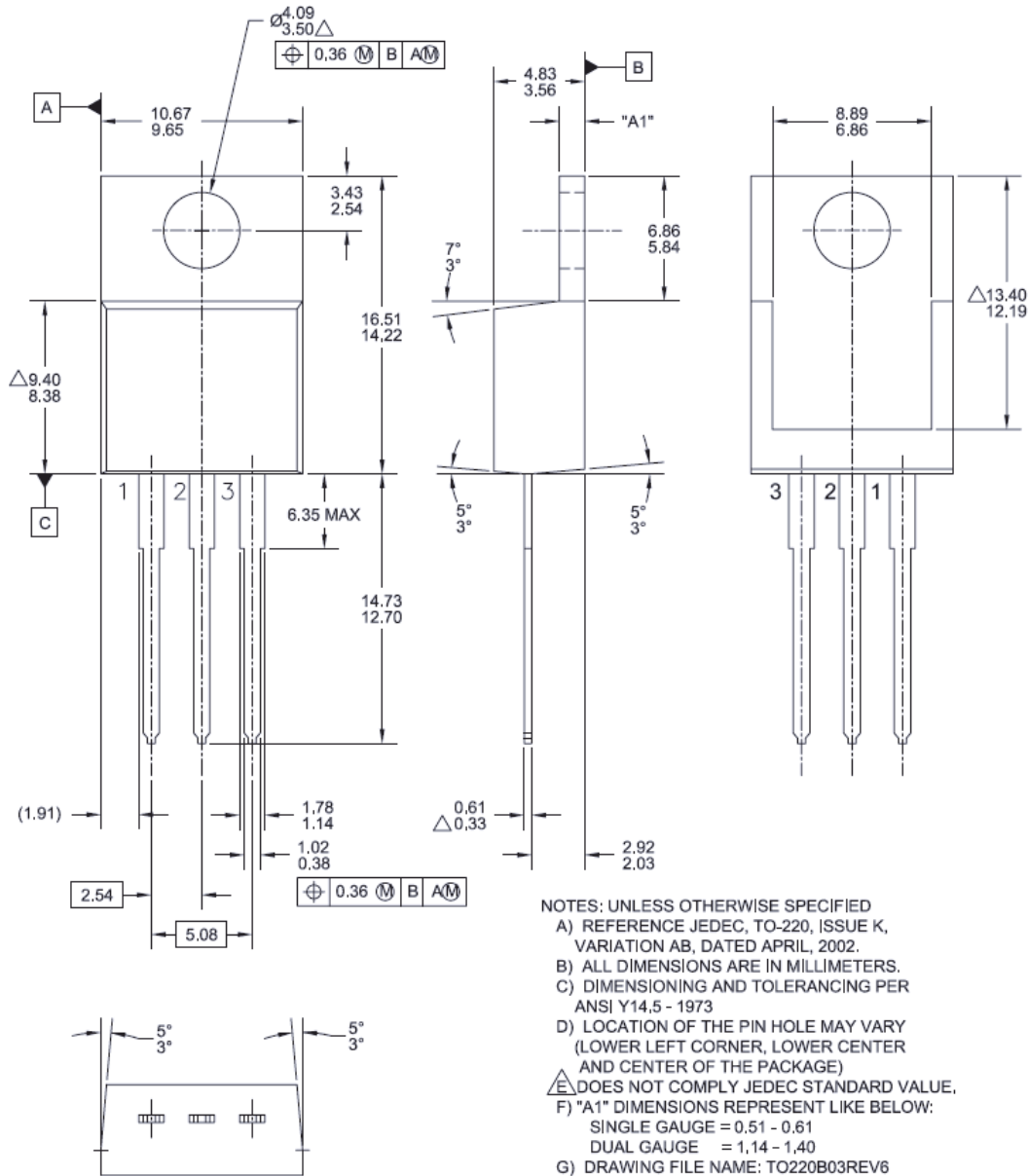


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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